

# 10V Drive Nch MOSFET

## R5016FNX

### ● Structure

Silicon N-channel MOSFET

### ● Features

- 1) Low on-resistance.
- 2) Low input capacitance.
- 3) High ESD.

### ● Application

Switching

### ● Packaging specifications

Type	Package	Bulk
	Code	-
	Basic ordering unit (pieces)	500
R5016FNX		○

### ● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	$V_{DSS}$	500	V	
Gate-source voltage	$V_{GSS}$	±30	V	
Drain current	Continuous	$I_D^{*3}$	±16	A
	Pulsed	$I_{DP}^{*1}$	±64	A
Source current (Body Diode)	Continuous	$I_S^{*3}$	16	A
	Pulsed	$I_{SP}^{*1}$	64	A
Avalanche current	$I_{AS}^{*2}$	8	A	
Avalanche energy	$E_{AS}^{*2}$	17.1	mJ	
Power dissipation	$P_D^{*4}$	50	W	
Channel temperature	$T_{ch}$	150	°C	
Range of storage temperature	$T_{stg}$	-55 to +150	°C	

\*1  $P_w \leq 10 \mu s$ , Duty cycle  $\leq 1\%$

\*2  $L = 500 \mu H$ ,  $V_{DD} = 50V$ ,  $R_G = 25 \Omega$ ,  $T_{ch} = 25^\circ C$

\*3 Limited only by maximum channel temperature allowed.

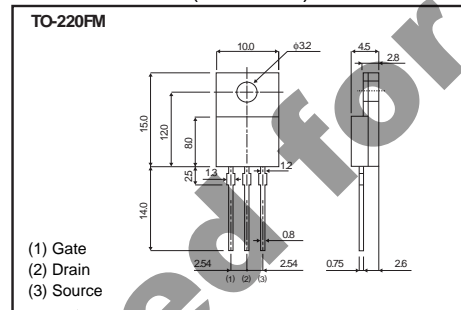
\*4  $T_C = 25^\circ C$

### ● Thermal resistance

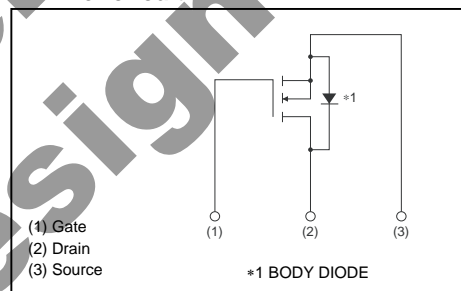
Parameter	Symbol	Limits	Unit
Channel to Case	$R_{th(ch-c)}^*$	2.5	°C / W

\*  $T_C = 25^\circ C$

### ● Dimensions (Unit : mm)



### ● Inner circuit



**●Electrical characteristics (Ta = 25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	±100	nA	$V_{GS}=\pm 30V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	500	-	-	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	-	-	100	μA	$V_{DS}=500V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	3.0	-	5.0	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	0.25	0.325	Ω	$I_D=8A, V_{GS}=10V$
Forward transfer admittance	$ Y_{fs} ^*$	6.2	11	-	S	$V_{DS}=10V, I_D=8A$
Input capacitance	$C_{iss}$	-	1700	-	pF	$V_{DS}=25V$
Output capacitance	$C_{oss}$	-	1000	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	-	35	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	35	-	ns	$V_{DD}=250V, I_D=8.0A$
Rise time	$t_r^*$	-	60	-	ns	$V_{GS}=10V$
Turn-off delay time	$t_{d(off)}^*$	-	110	-	ns	$R_L=31.25\Omega$
Fall time	$t_f^*$	-	35	-	ns	$R_G=10\Omega$
Total gate charge	$Q_g^*$	-	46	-	nC	$V_{DD}=250V$
Gate-source charge	$Q_{gs}^*$	-	11	-	nC	$I_D=8.0A$
Gate-drain charge	$Q_{gd}^*$	-	19	-	nC	$V_{GS}=10V$

\*Pulsed

**●Body diode characteristics (Source-Drain)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{SD}^*$	-	-	1.5	V	$I_S=16A, V_{GS}=0V$
Reverse recovery time	$t_{rr}^*$	75	100	125	ns	$I_S=16A, V_{GS}=0V$ $di/dt=100A/\mu s$

\*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics ( I )

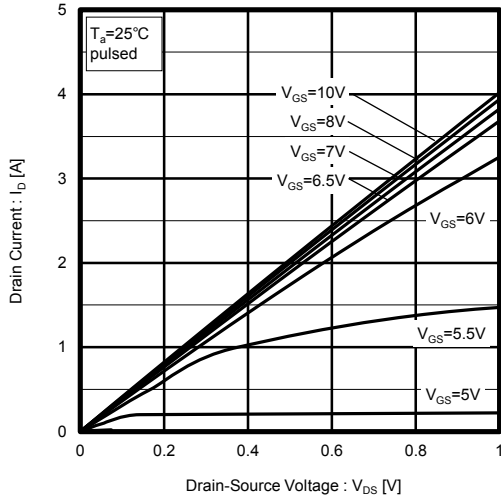


Fig.2 Typical Output Characteristics ( II )

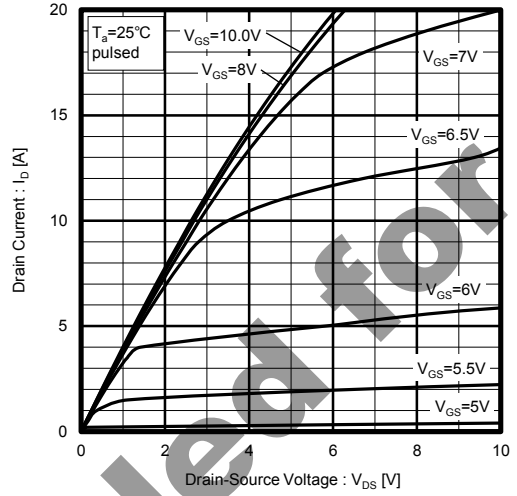


Fig.3 Typical Transfer Characteristics

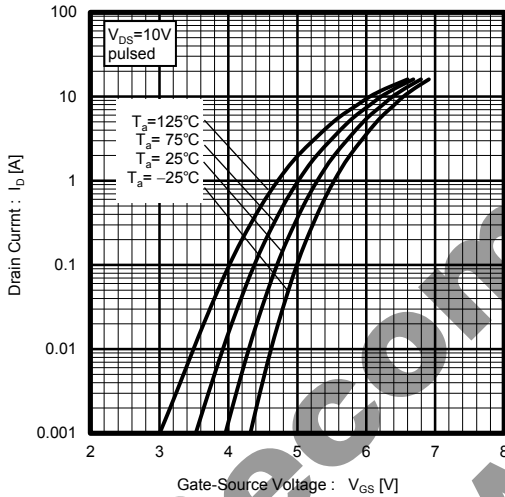


Fig.4 Gate Threshold Voltage vs. Channel Temperature

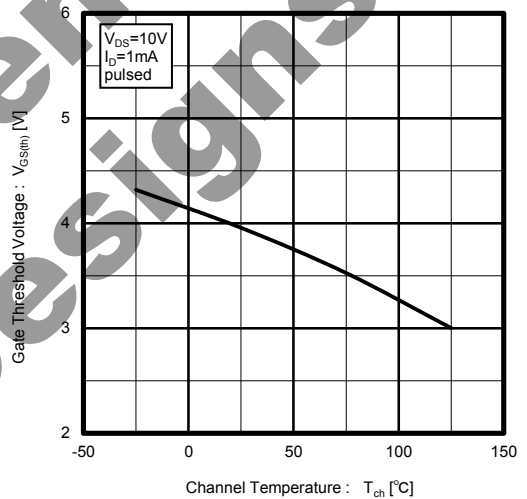


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

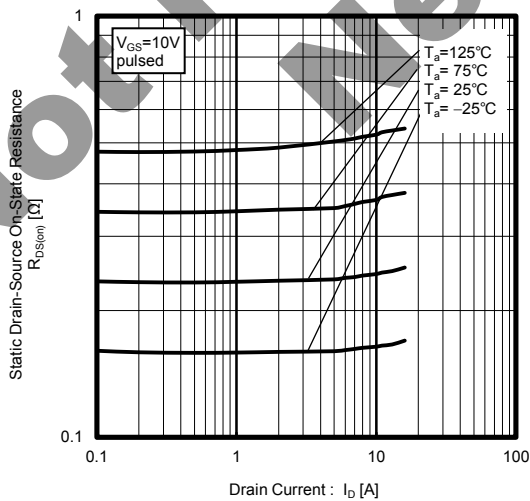


Fig.6 Static Drain-Source On-State Resistance vs. Channel Temperature

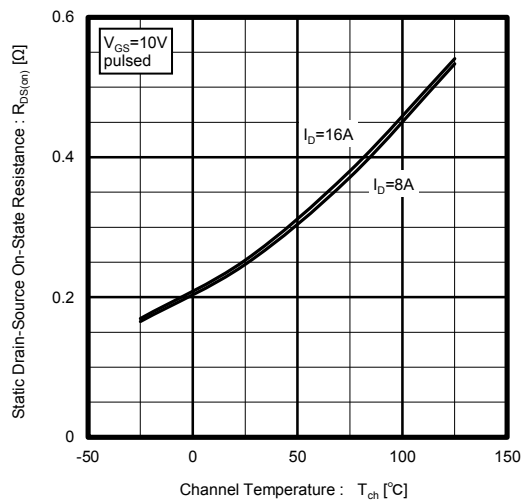


Fig.7 Forward Transfer Admittance vs. Drain Current

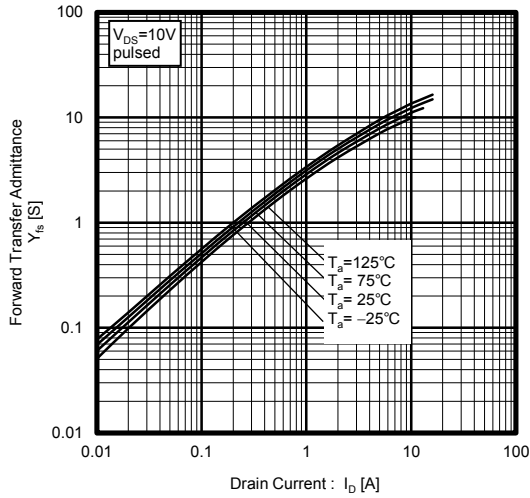


Fig.8 Source Current vs. Source-Drain Voltage

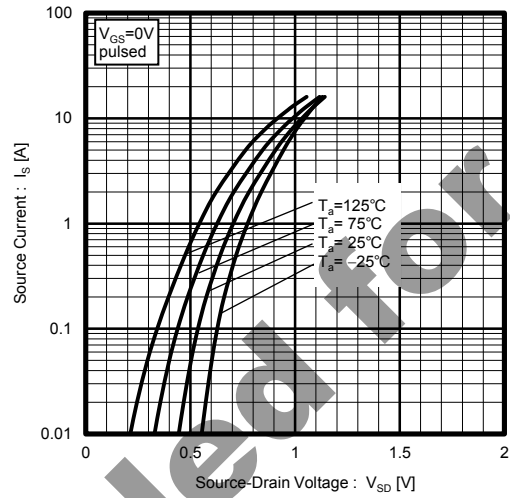


Fig.9 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

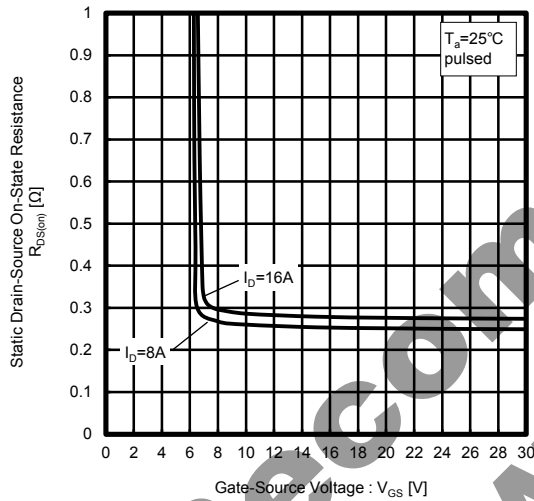


Fig.10 Switching Characteristics

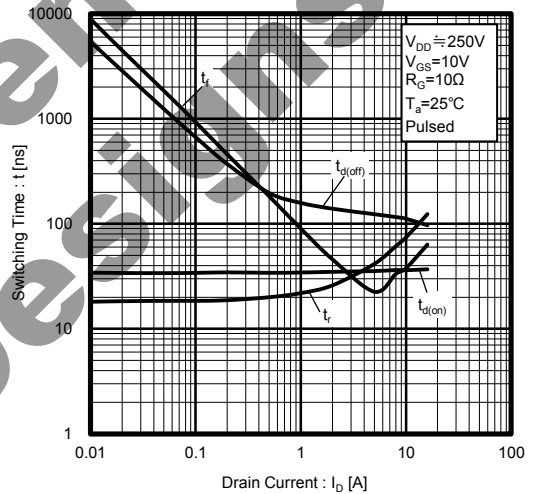


Fig.11 Dynamic Input Characteristics

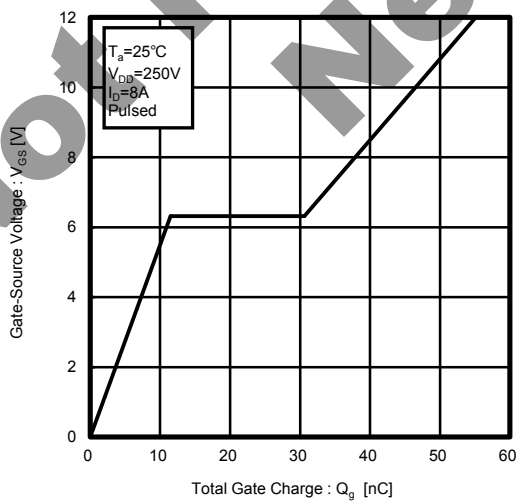


Fig.12 Typical Capacitance vs. Drain-Source Voltage

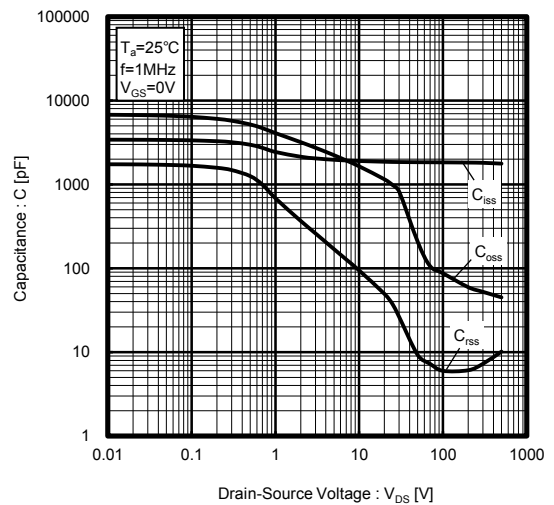


Fig.13 Normalized Transient Thermal Resistance v.s. Pulse Width

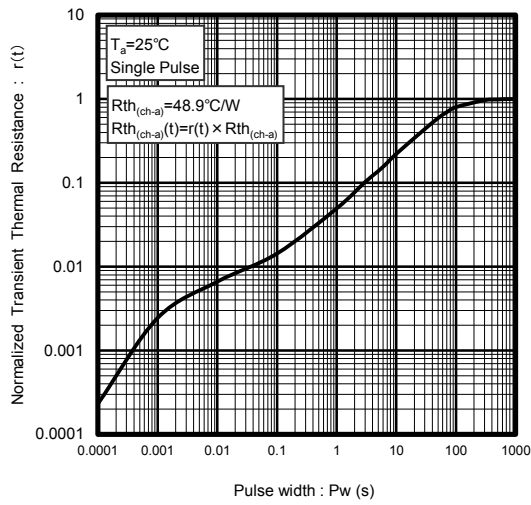


Fig.14 Maximum Safe Operating Area

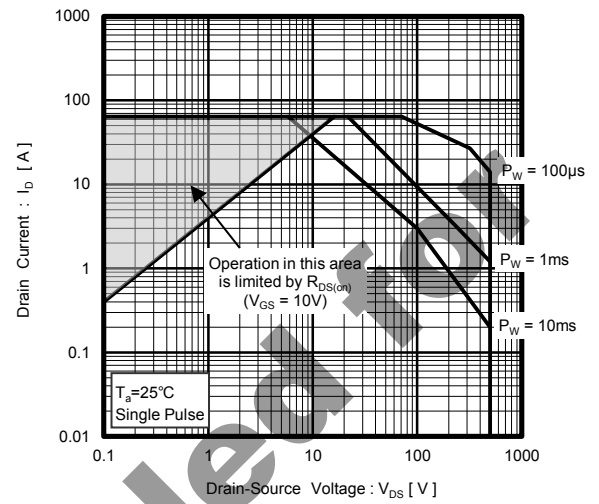
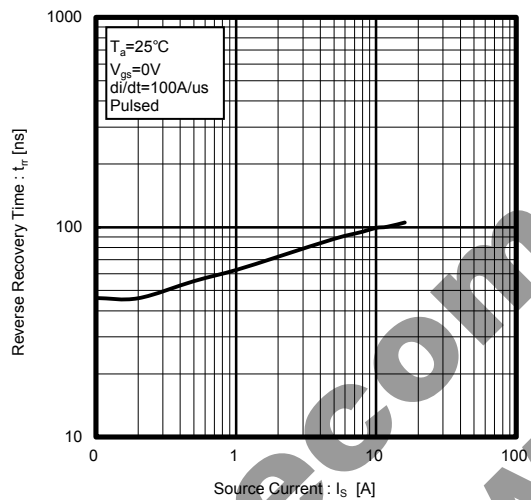


Fig.15 Reverse Recovery Time vs. Source Current



Not Recommended for New Designs

● Measurement circuits

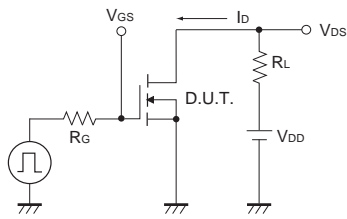


Fig.1-1 Switching Time Measurement Circuit

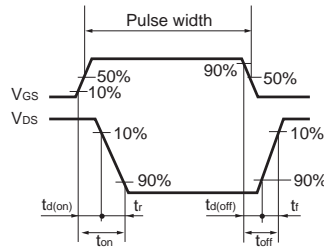


Fig.1-2 Switching Waveforms

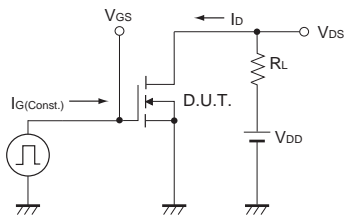


Fig.2-1 Gate Charge Measurement Circuit

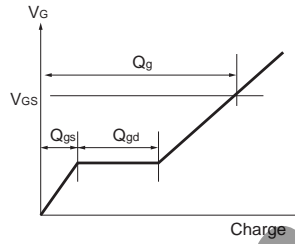


Fig.2-2 Gate Charge Waveform

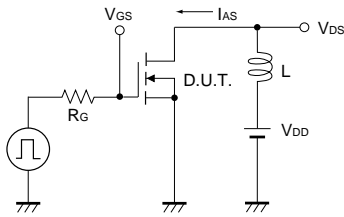


Fig.3-1 Avalanche Measurement Circuit

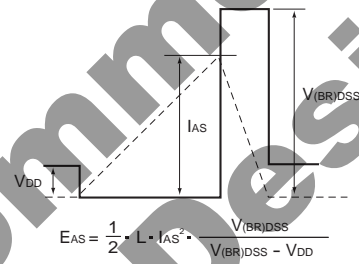


Fig.3-2 Avalanche Waveform

Not Recommended for New Designs

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